

N-Channel 800V (D-S) Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	800
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$ 1.3
Q_g (Max.) (nC)	33
Q_{gs} (nC)	6
Q_{gd} (nC)	17
Configuration	Single

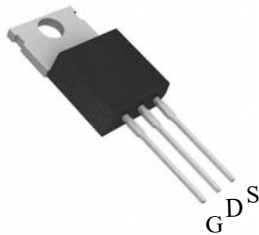
FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC

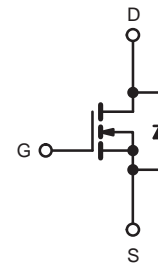
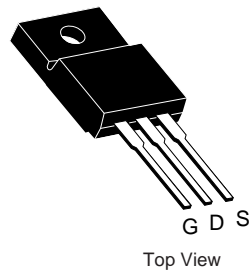


Available
RoHS*
COMPLIANT

TO-220 Pin Configuration



TO-220 FULLPAK



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25\text{ }^\circ\text{C}$	7
		$T_C = 100\text{ }^\circ\text{C}$	
Pulsed Drain Current ^a		I_{DM}	28
Linear Derating Factor			1.5
Single Pulse Avalanche Energy ^b		E_{AS}	650
Repetitive Avalanche Current ^a		I_{AR}	7.8
Repetitive Avalanche Energy ^a		E_{AR}	19
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	190
Peak Diode Recovery dV/dt ^c		dV/dt	5.0
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d
Mounting Torque	6-32 or M3 screw		10
			1.1

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 23\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 7.8\text{ A}$ (see fig. 12).
- $I_{SD} \leq 7.8\text{ A}$, $dI/dt \leq 140\text{ A}/\mu\text{s}$, $V_{DD} \leq 600\text{ V}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

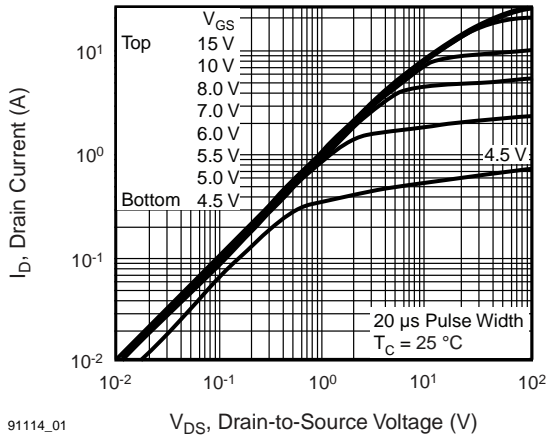
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.65	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		800	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.98	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	45	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 3.7\text{ A}^b$	-	1.3	1.8	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 100\text{ V}, I_D = 3.7\text{ A}^b$		4.5	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz}$, see fig. 5		-	1120	-	pF
Output Capacitance	C_{oss}			-	115	-	
Reverse Transfer Capacitance	C_{riss}			-	27	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 3.8\text{ A}, V_{DS} = 400\text{ V},$ see fig. 6 and 13 ^b	-	-	33	nC
Gate-Source Charge	Q_{gs}			-	-	6	
Gate-Drain Charge	Q_{gd}			-	-	17	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 3.8\text{ A},$ $R_g = 6.2\text{ }\Omega, R_D = 52\text{ }\Omega$ see fig. 10 ^b		-	18	-	ns
Rise Time	t_r			-	30	-	
Turn-Off Delay Time	$t_{d(off)}$			-	76	-	
Fall Time	t_f			-	33	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	5.0	-	nH
Internal Source Inductance	L_S			-	13	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	5.0	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	21	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 3.8\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.8	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 3.8\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}^b$		-	380	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	4.0	-	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

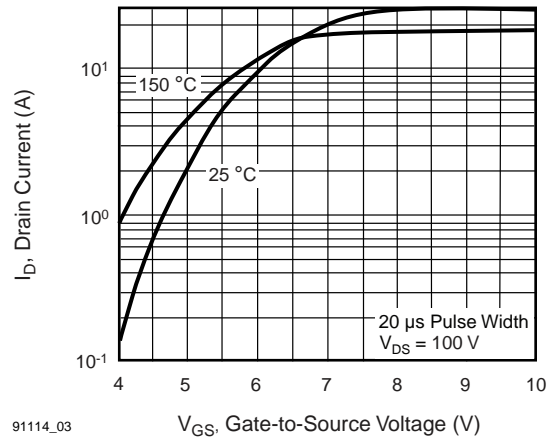
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



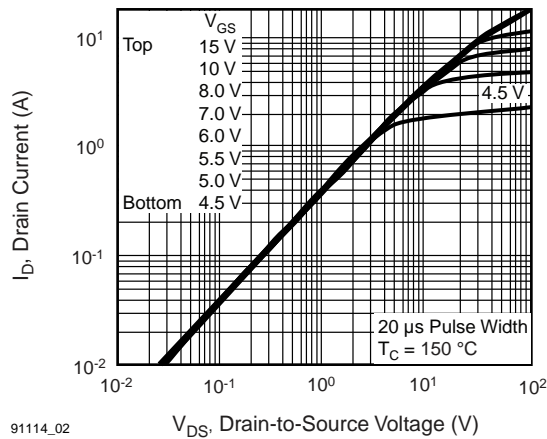
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Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$



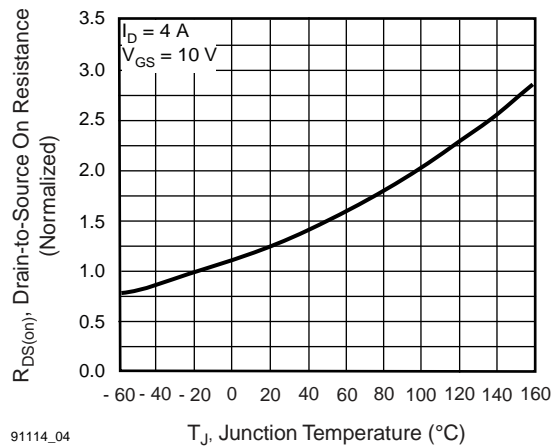
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Fig. 3 - Typical Transfer Characteristics



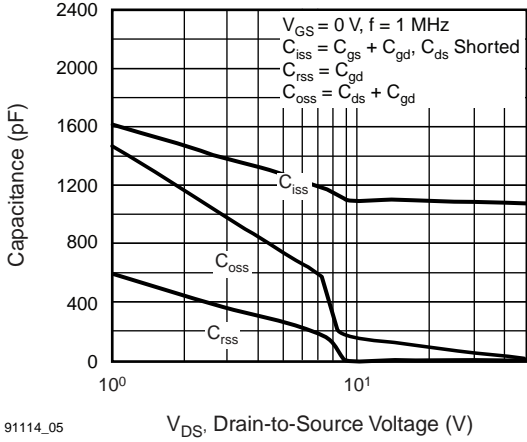
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Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$



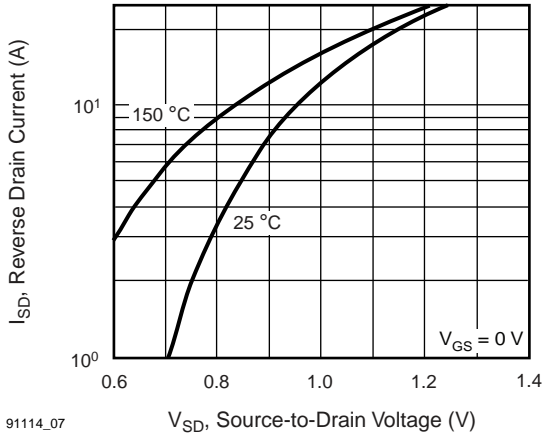
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Fig. 4 - Normalized On-Resistance vs. Temperature



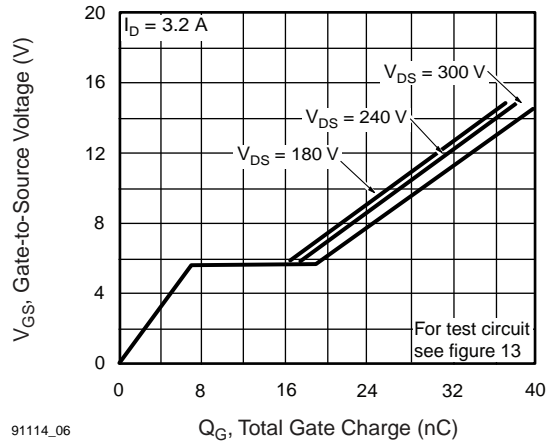
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



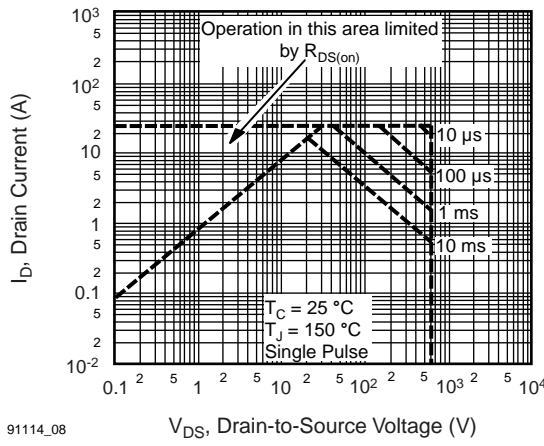
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



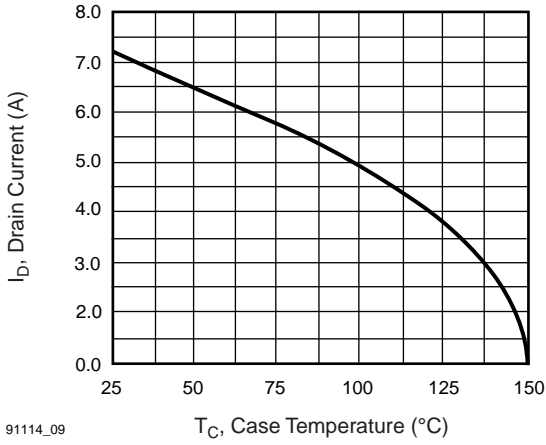
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Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91114_08

Fig. 8 - Maximum Safe Operating Area



91114_09

Fig. 9 - Maximum Drain Current vs. Case Temperature

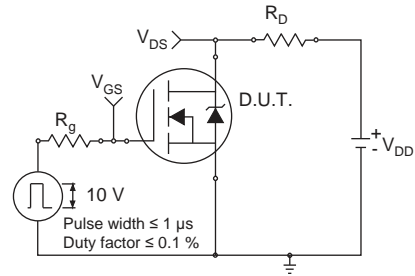


Fig. 10a - Switching Time Test Circuit

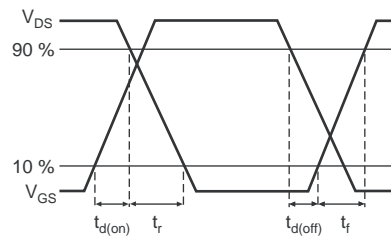
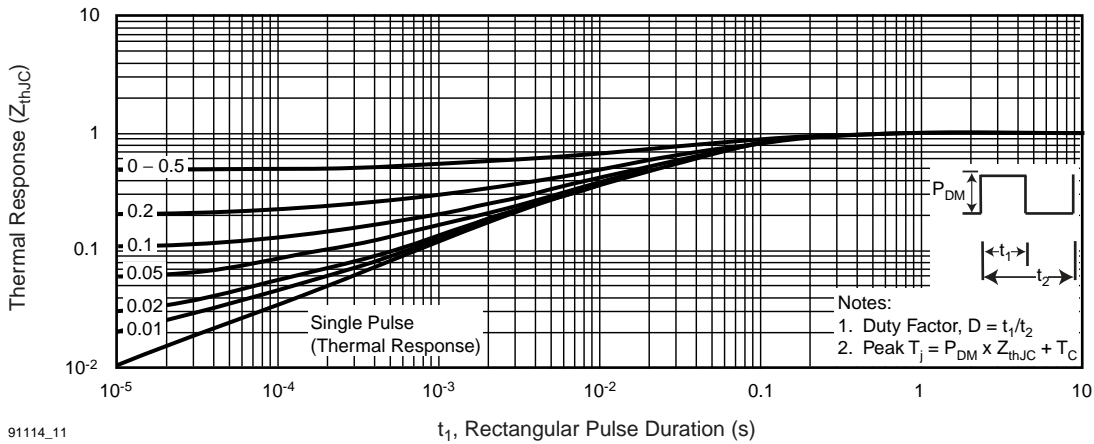


Fig. 10b - Switching Time Waveforms



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Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

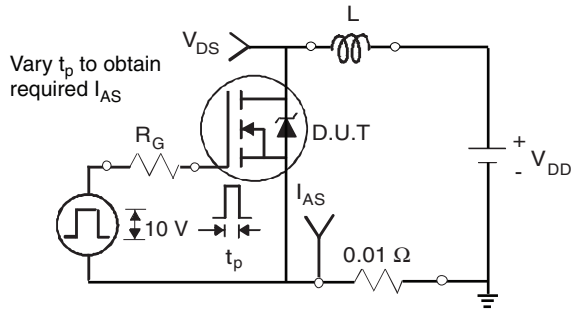


Fig. 12a - Unclamped Inductive Test Circuit

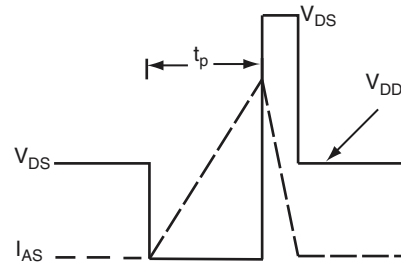


Fig. 12b - Unclamped Inductive Waveforms

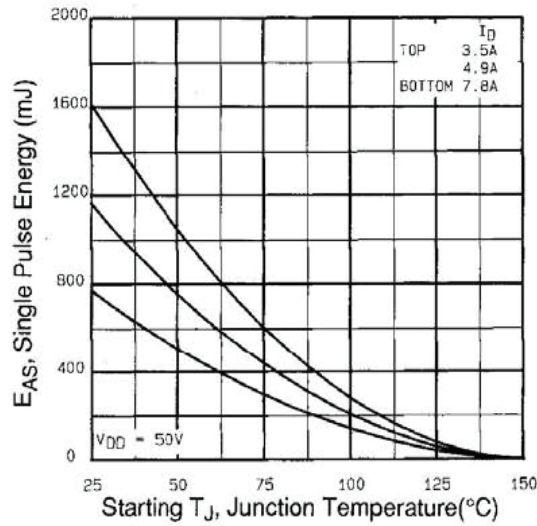


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

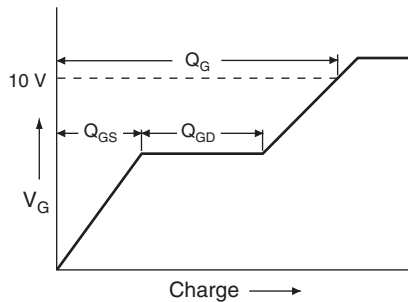


Fig. 13a - Basic Gate Charge Waveform

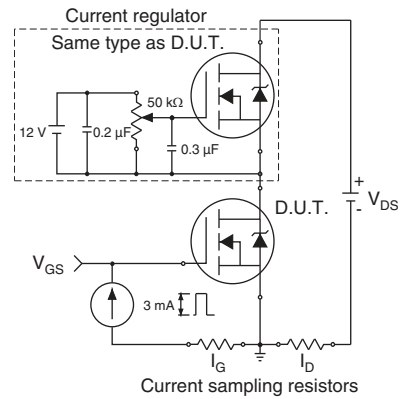
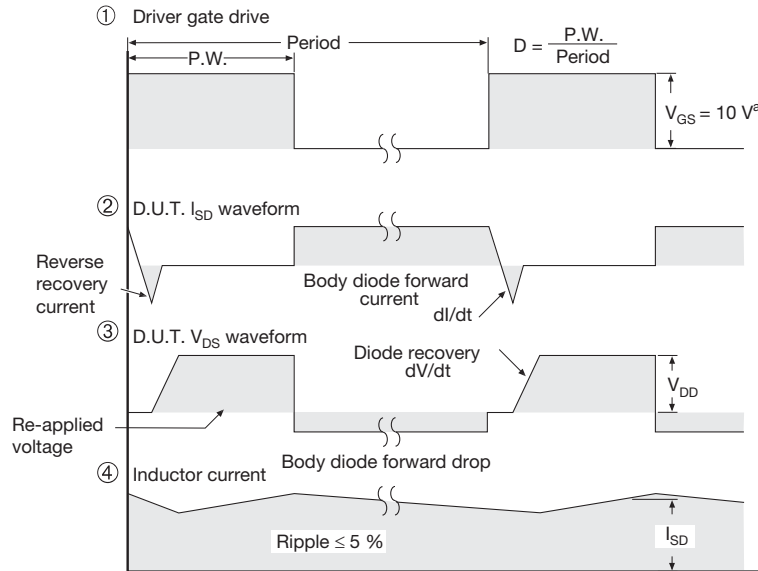
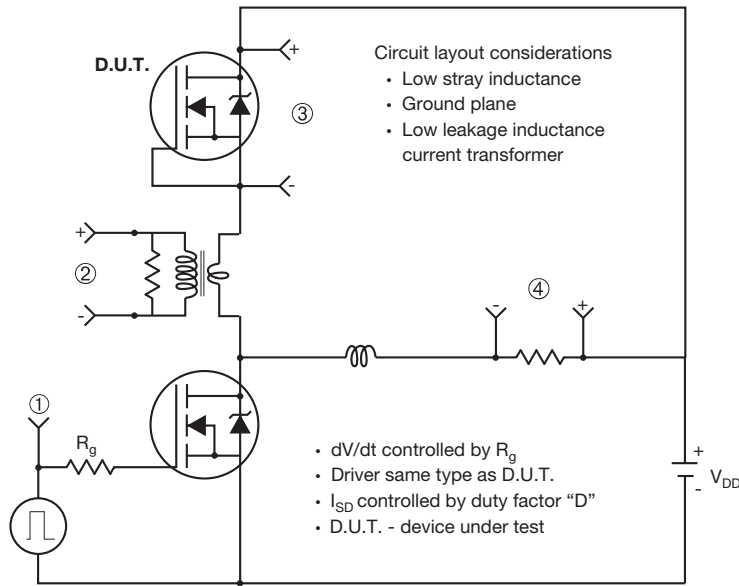


Fig. 13b - Gate Charge Test Circuit

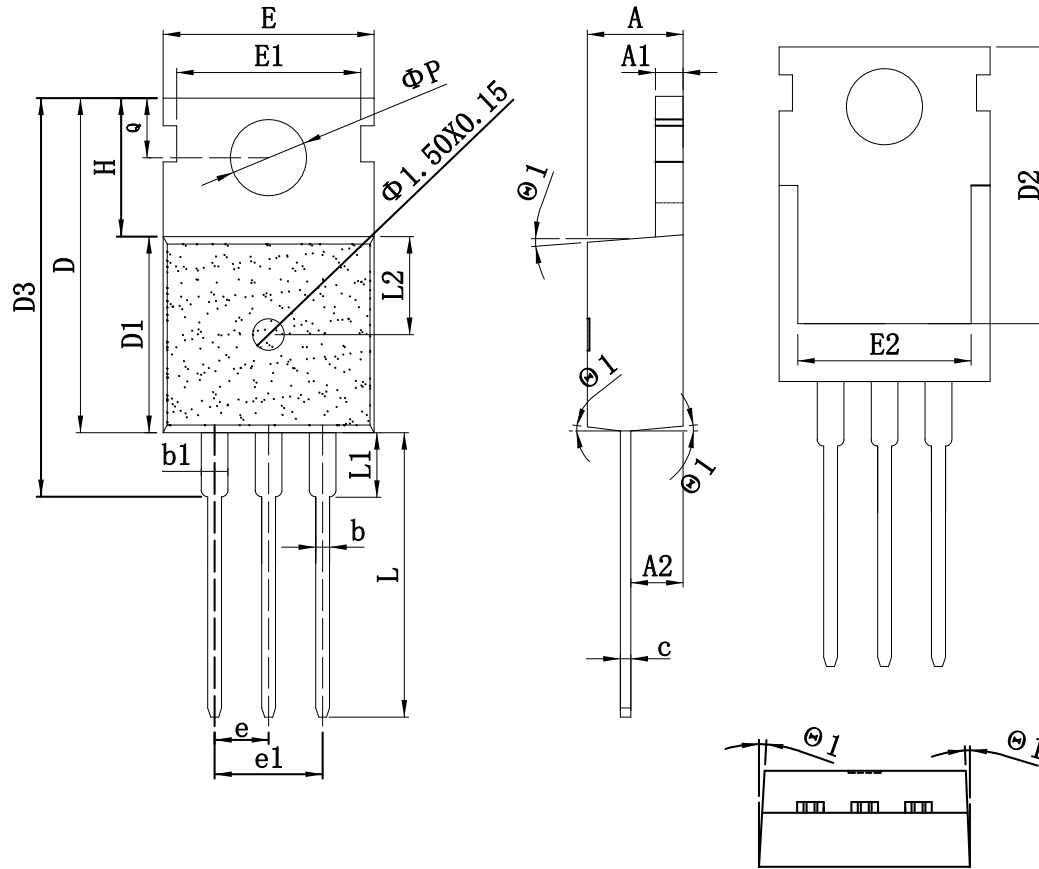
Peak Diode Recovery dV/dt Test Circuit



Note
a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

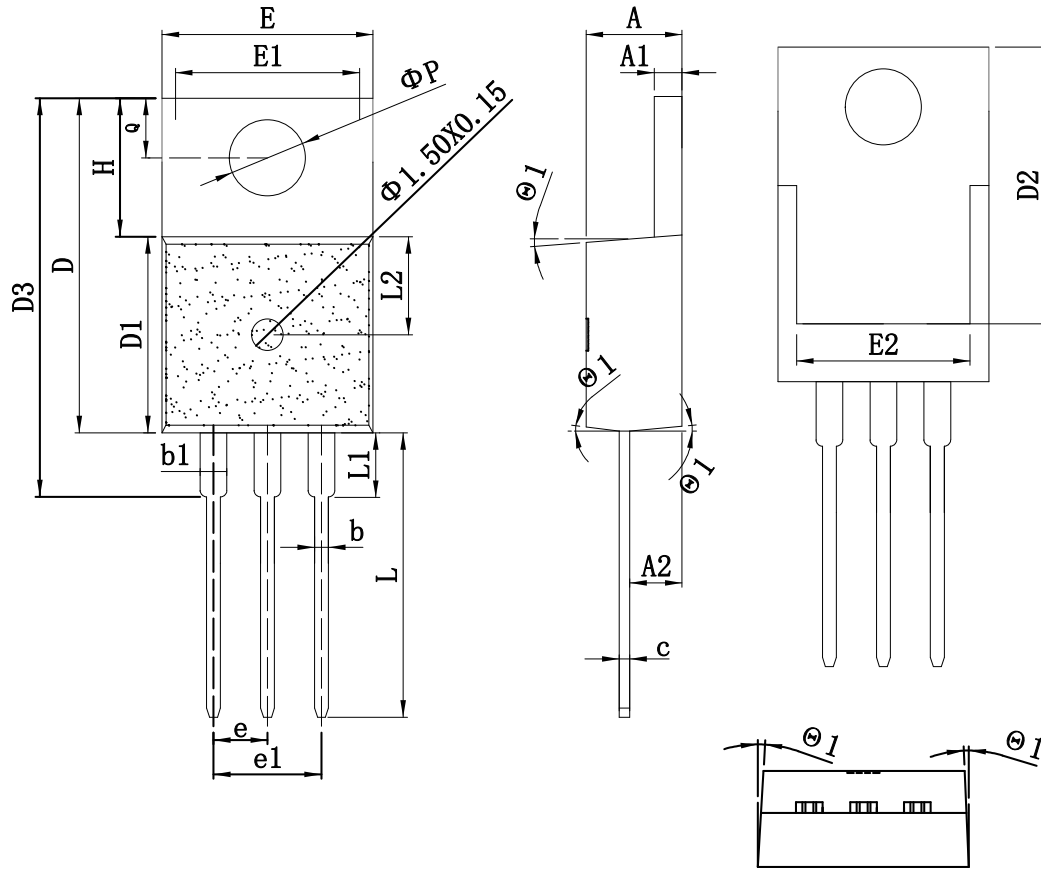
TO-220_3L-A PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
	MIN	TYP	MAX		MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	H	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	ϕP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
E	8.68	10.02	11.00	θ	2°	-	7°

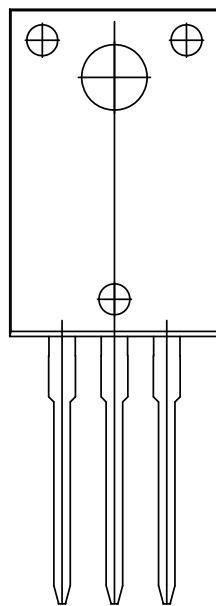
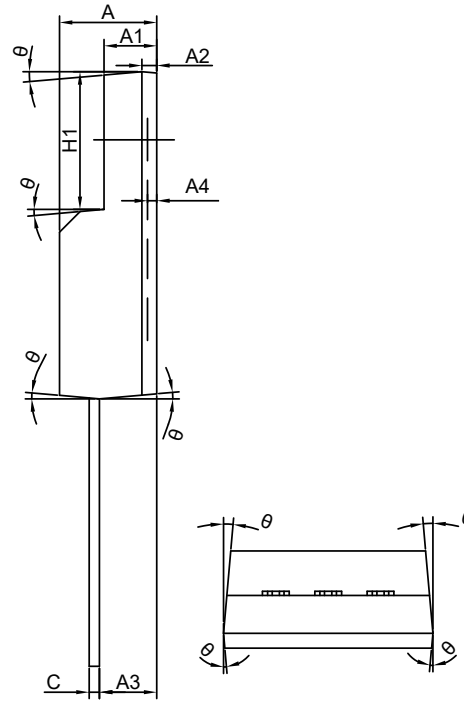
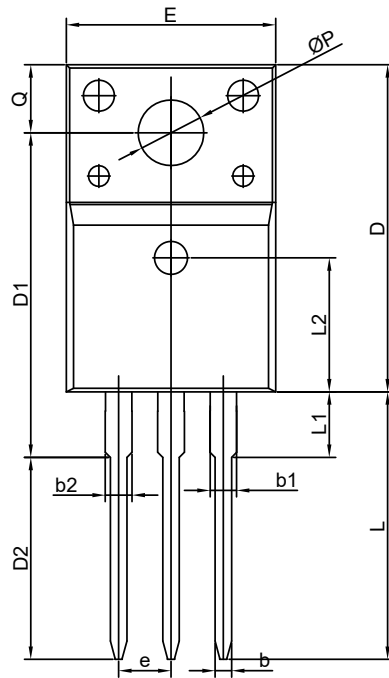
TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
	MIN	TYP	MAX		MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	H	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	ϕP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
E	8.68	10.02	11.00	θ	2°	-	7°

TO-220F-3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.30	4.72	5.10
A1	2.25	2.56	2.90
A2	0.72 REF		
A3	2.28	2.78	3.50
A4	0.45 MAX		
b	0.65	-	0.95
b1	1.00	-	1.55
b2	-	-	1.55
c	0.40	0.50	0.65
D	15.47	15.87	16.37
D1	15.35	15.75	16.25
E	9.76	10.16	10.76
e	2.54 BSC		
H1	6.28	6.68	7.08
L	12.48	12.98	13.50
L1	2.90	-	3.80
L2	2.54 BSC		
ØP	2.98	3.18	3.50
Q	3.00	-	3.60
θ	3°	5°	7°

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